

- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

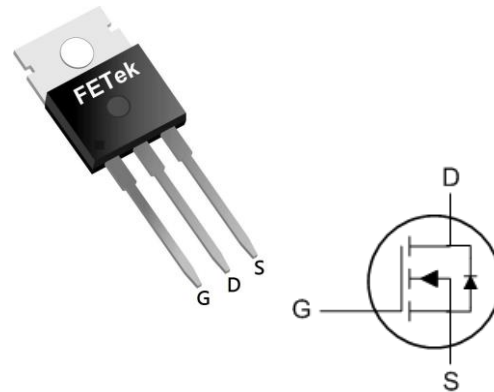
Product Summary


BVDSS	RDSON	ID
80V	12mΩ	100A

Description

The FKP8016 is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The FKP8016 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO220 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	80	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current ¹	100	A
$I_D@T_C=100^\circ C$	Continuous Drain Current ¹	70	A
I_{DM}	Pulsed Drain Current ²	200	A
EAS	Single Pulse Avalanche Energy ³	80	mJ
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	89	W
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.65	$^\circ C/W$

**Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	80	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=20A$	---	9.6	12	$m\Omega$
		$V_{GS}=4.5V, I_D=10A$	---	12	14.5	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	---	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=64V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=64V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=10A$	---	32	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	0.66	---	Ω
Q_g	Total Gate Charge (10V)	$V_{DS}=64V, V_{GS}=10V, I_D=10A$	---	60.9	---	nC
Q_{gs}	Gate-Source Charge		---	8.1	---	
Q_{gd}	Gate-Drain Charge		---	17.9	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=40V, V_{GS}=10V, R_G=3.3\Omega, I_D=10A$	---	12.2	---	ns
T_r	Rise Time		---	24.5	---	
$T_{d(off)}$	Turn-Off Delay Time		---	50.5	---	
T_f	Fall Time		---	17.6	---	
C_{iss}	Input Capacitance	$V_{DS}=50V, V_{GS}=0V, f=1\text{MHz}$	---	3120	---	pF
C_{oss}	Output Capacitance		---	140	---	
C_{rss}	Reverse Transfer Capacitance		---	110	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	100	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=10A, di/dt=100A/\mu s$,	---	18.6	---	nS
Q_{rr}	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	65	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=50V, V_{GS}=10V, L=0.1mH, I_{AS}=40A$
- 4.The power dissipation is limited by 175°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

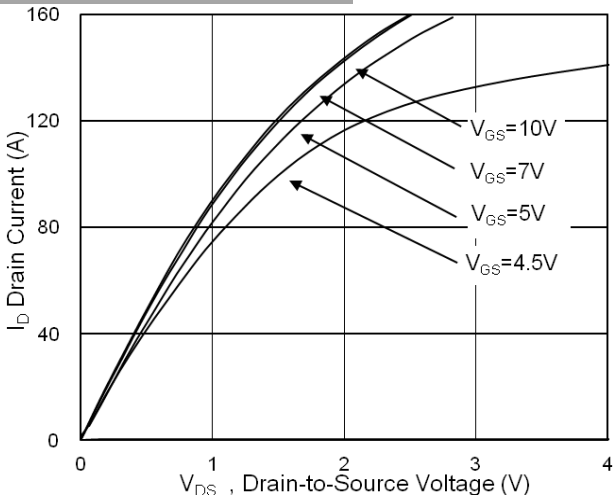


Fig.1 Typical Output Characteristics

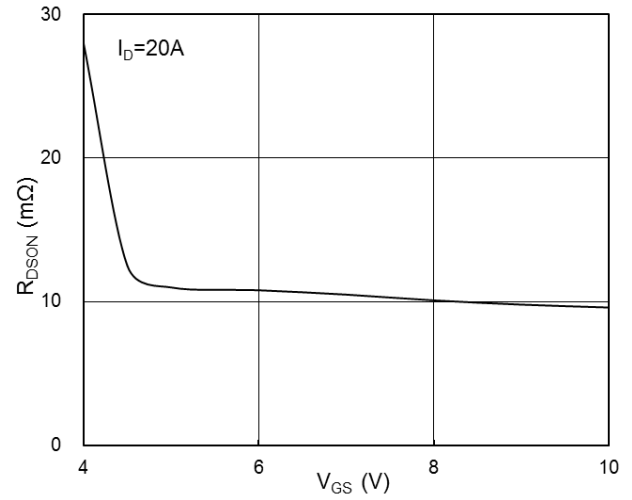


Fig.2 On-Resistance v.s Gate-Source

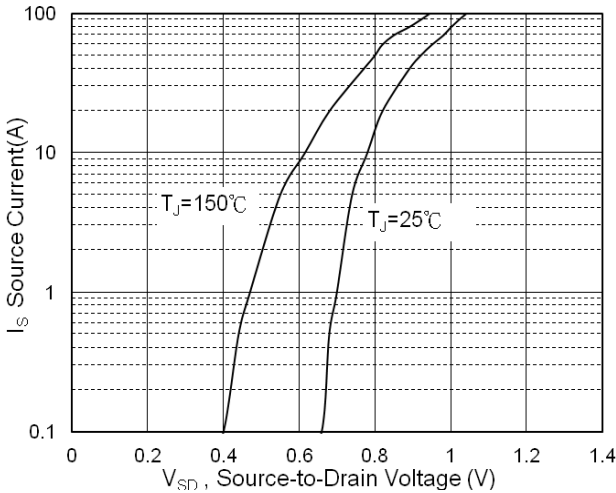


Fig.3 Forward Characteristics of Reverse

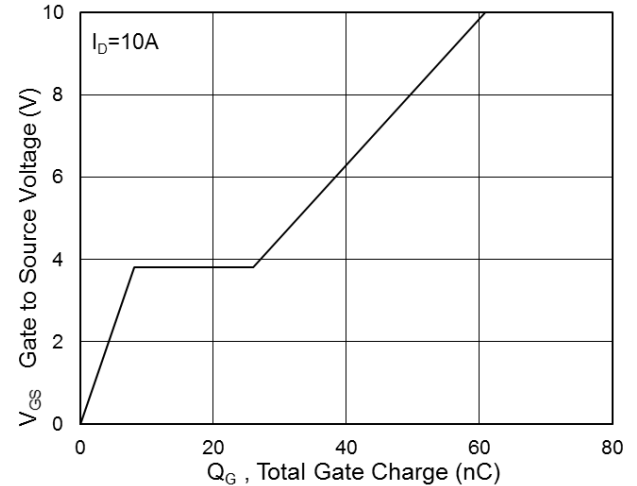


Fig.4 Gate-Charge Characteristics

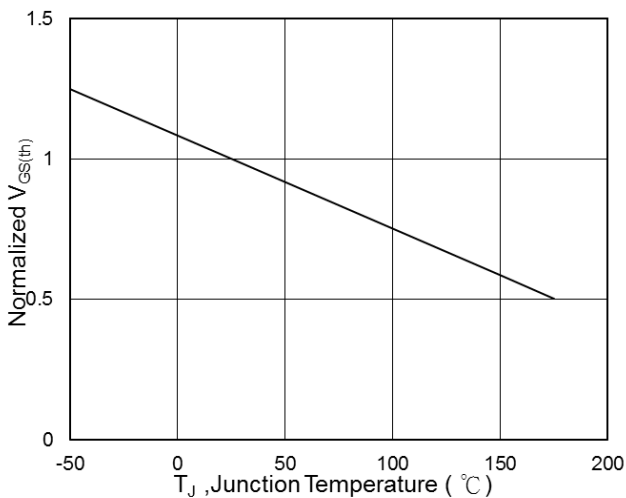


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

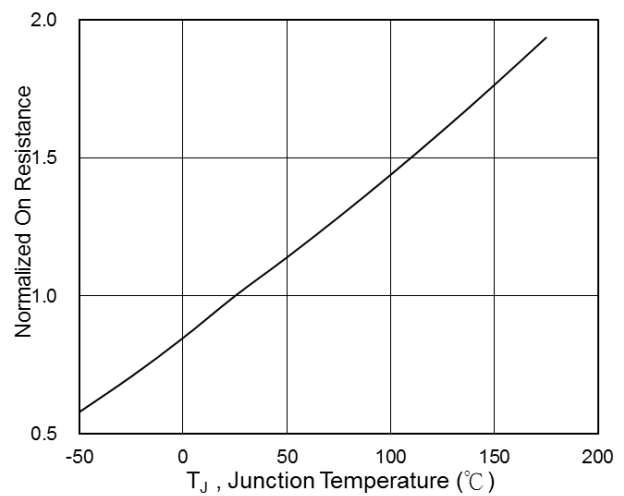


Fig.6 Normalized $R_{DS(ON)}$ vs. T_J

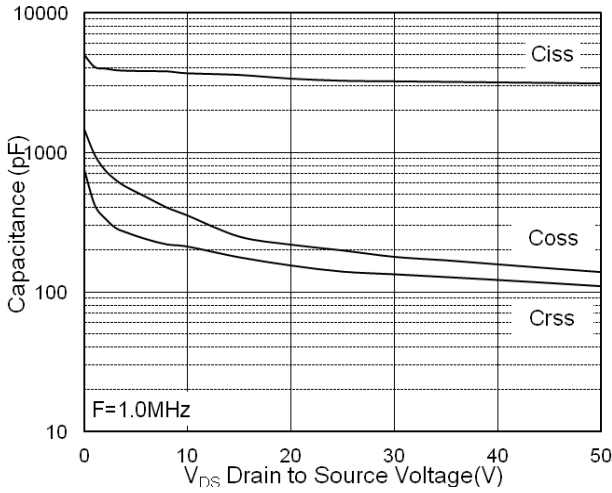


Fig.7 Capacitance

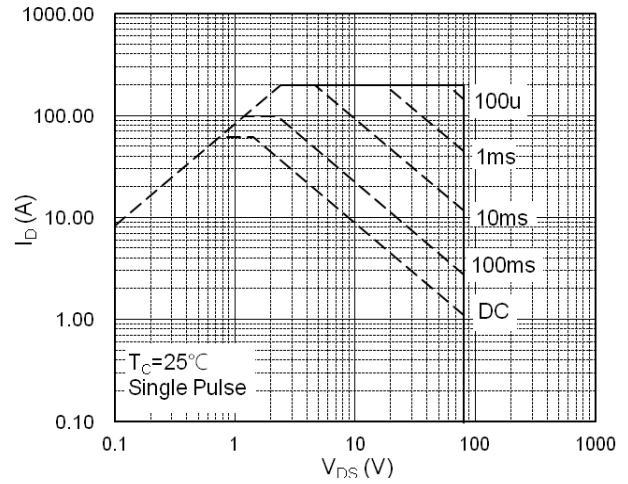


Fig.8 Safe Operating Area

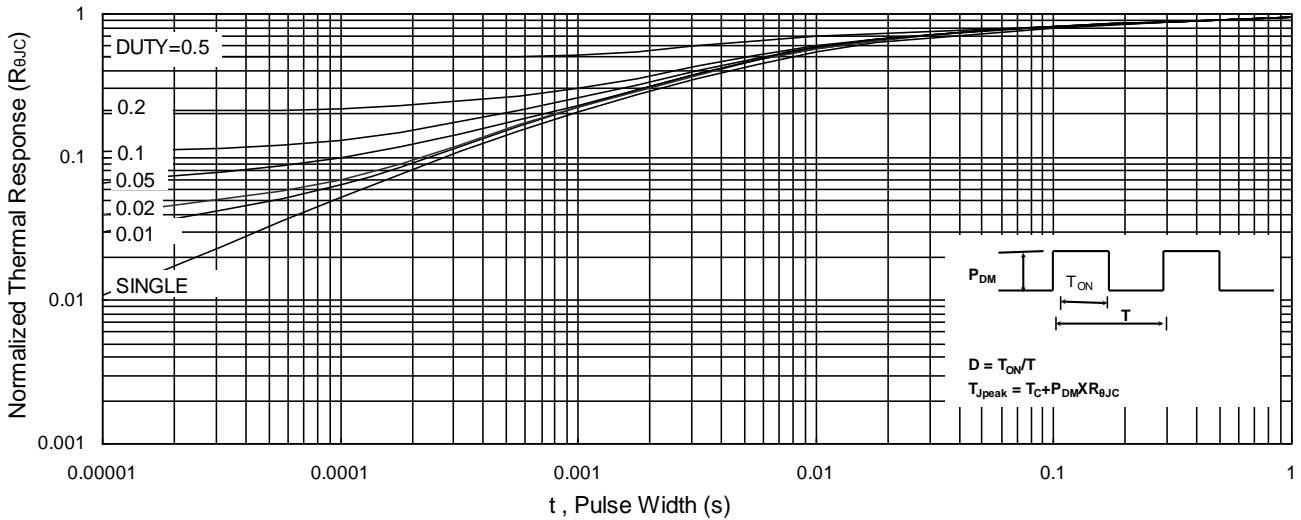


Fig.9 Normalized Maximum Transient Thermal Impedance

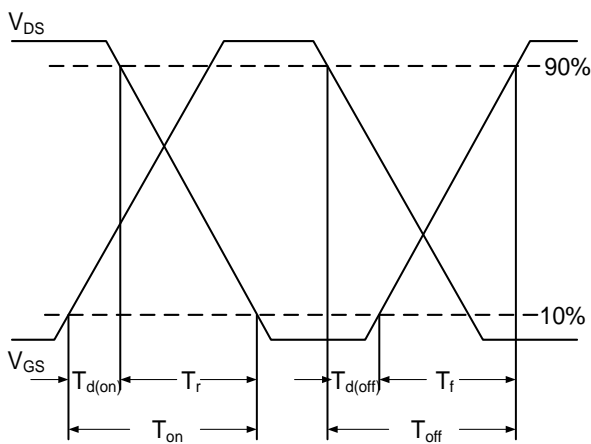


Fig.10 Switching Time Waveform

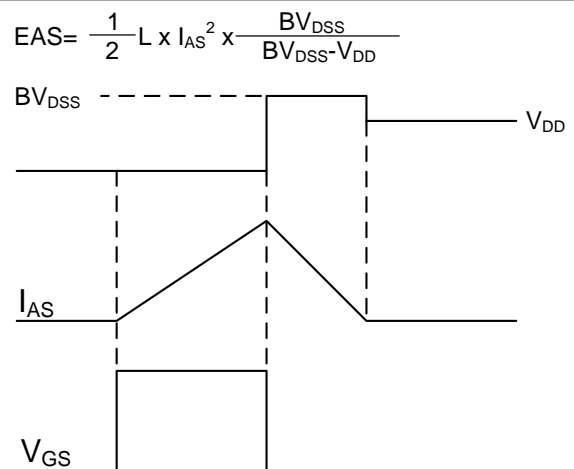


Fig.11 Unclamped Inductive Switching Waveform